

**IN UNITED STATES PATENT AND TRADEMARK OFFICE**

Patent No.: 6,806,095

Docket No: 7017/ETCH/CONE

Issue Date: October 19, 2004

Patentee: Nallan, et al.

Title           **METHOD OF PLASMA ETCHING OF HIGH-K DIELECTRIC  
MATERIALS WITH HIGH SELECTIVITY TO UNDERLYING LAYERS**

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**REQUEST FOR CERTIFICATION OF CORRECTION**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. A copy of the text of the Certificate in the suggested form is attached.

The fee of \$100.00 has been paid with the submission of this paper using the Patent Electronic Business Center. The Commissioner is authorized to charge any additional fees to Deposit Account No. 20-0782.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

Respectfully submitted,

Oct 17, 2006



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**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

PATENT NO : 6,806,095

DATED : October 19, 2004

INVENTOR(S) : Nallan et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (56), under "Foreign Patent Documents", in column 2, line1, after "12/2001" insert - - H01L - -.

In column 1, line 46, delete "HfO2, ZrO2" and insert - - HfO<sub>2</sub>, ZrO<sub>2</sub> - -, therefor.

In column 1, line 47, delete "HfSiO<sub>2</sub>" and insert - - HfSiO<sub>2</sub> - -, therefor.

In column 1, line 53, delete "Cl<sub>2</sub>/CO" and insert - - Cl<sub>2</sub>/CO - -, therefor.

In columns 3-4, lines 66-67 and 1-2, below "The foregoing steps of the..... dielectric layer." delete "The foregoing steps of the..... dielectric layer.".

(Repeated occurrence)

In column 4, line 40, delete "3500° C" and insert - - 350° C - -, therefor.

In column 4, line 64, delete "hafniumoxide" and insert - - hafnium-oxide - -, therefor.

In column 6, line 10, in Claim 11, delete "A" before "The".

In column 6, line 16, in Claim 12, after "material" insert - - , - -.

In column 6, line 39, In Claim 17, after "gas," insert - - and - -.

MAILING ADDRESS OF SENDER:

PATENT NO. 6,806,095

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